

# PRELIMINARY

Notice : This is not a final specification  
Some parametric are subject to change.

# RTE05N3M-T151

Composite Transistor  
Zener Diode

Resistor Built-in Transistor Silicon NPN Epitaxial Type

AEC-Q101 Compliance

## DESCRIPTION

RTE05N3M is a composite transistor built RT1N441 and Zener diode ( $V_z=3.6V$ ) in SC-88 package.

Use of this product enables miniaturization of equipment and reduction parts and process.

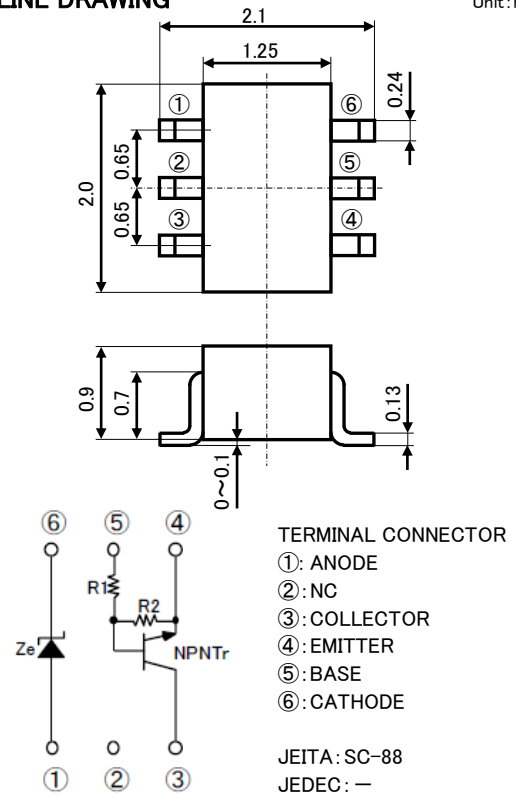
## FEATURE

- This product is packaged in super mini PKG(6pin) and mount RT1N441( $R_1=47k\Omega$ ,  $R_2=47k\Omega$ ) and Zener diode ( $V_z=3.6V$ ).
- Enables miniaturization of equipment and high density mounting.

## APPLICATION

Power supply circuit  
Driver circuit

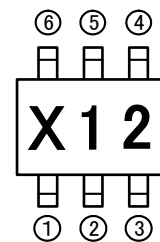
## OUTLINE DRAWING



## MAXIMUM RATING ( $T_a=25^\circ C$ )

SYMBOL	PARAMETER	RATING	UNIT
$V_{CBO}$	Collector to Base voltage	50	V
$V_{EBO}$	Emitter to Base voltage	10	V
$V_{CEO}$	Collector to Emitter voltage	50	V
$V_{IN}$	Input voltage	40	V
$I_C$	Collector current	100	mA
$I_{CM}$	Peak Collector current	200	mA
$P_T$	Total dissipation	150	mW
$T_j$	Junction temperature	+150	$^\circ C$
$T_{stg}$	Storage temperature	-55~+150	$^\circ C$

## MARKING



## ELECTRICAL CHARACTERISTICS ( $T_a=25^\circ C$ )

SYMBOL	PARAMETER	TEST CONDITIONS	LIMITS			UNIT
			MIN	TYP	MAX	
$I_{CBO}$	Collector cut off current	$V_{CB}=50V$ , $I_E=0A$	-	-	0.1	$\mu A$
$I_{EBO}$	Emitter cut off current	$V_{EB}=5V$ , $I_C=0A$	41	53	76	$\mu A$
$h_{FE}$	DC forward current gain	$V_{CE}=5V$ , $I_C=5mA$	50	-	-	-
$V_{CE(sat)}$	Collector to Emitter saturation voltage	$I_C=10mA$ , $I_B=0.5mA$	-	-	0.3	V
$V_{I(ON)}$	Input on voltage	$V_{CE}=0.2V$ , $I_C=5mA$	-	2.2	5.0	V
$V_{I(OFF)}$	Input off voltage	$V_{CE}=5V$ , $I_C=100\mu A$	0.8	1.1	-	V
$R_1$	Input resistor	-	33	47	61	$k\Omega$
$R_2/R_1$	Resistor ratio	-	0.9	1.0	1.1	-
$f_T$	Gain band width product	$V_{CE}=6V$ , $I_E=-10mA$	-	200	-	MHz
$V_Z$	Zener voltage	$I_Z=5mA$	3.4	-	3.8	V
$I_R$	Reverse current	$V_R=1V$	-	-	20	$\mu A$

# PRELIMINARY

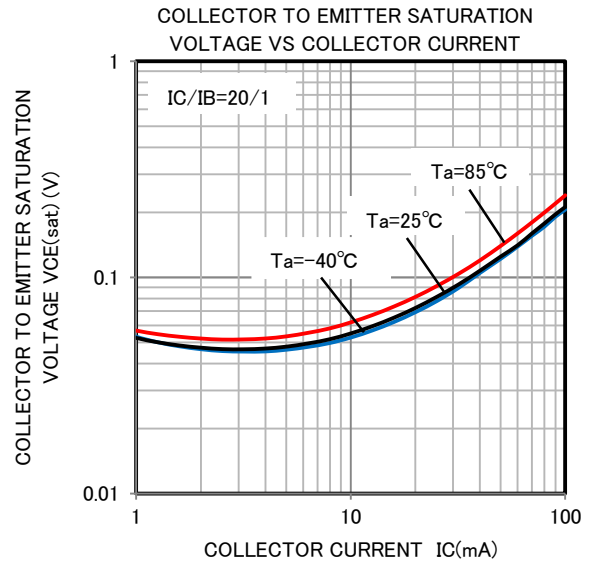
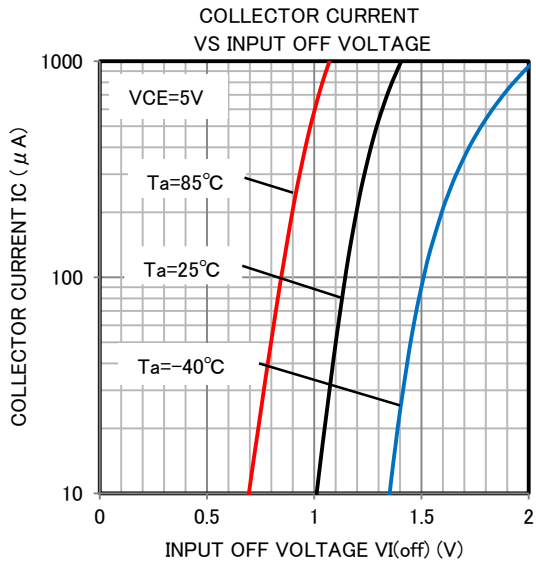
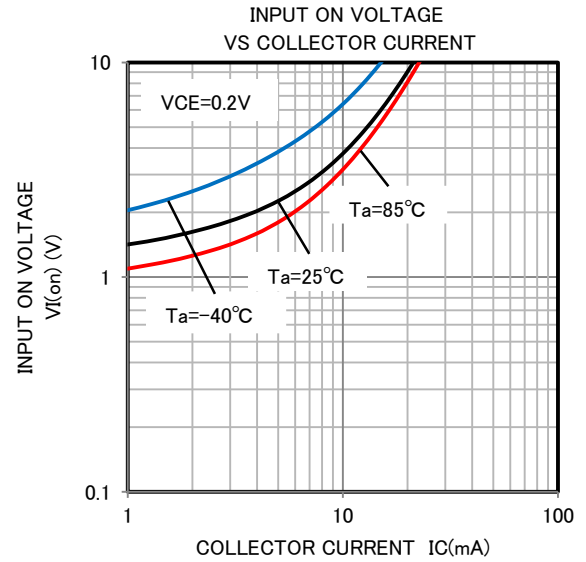
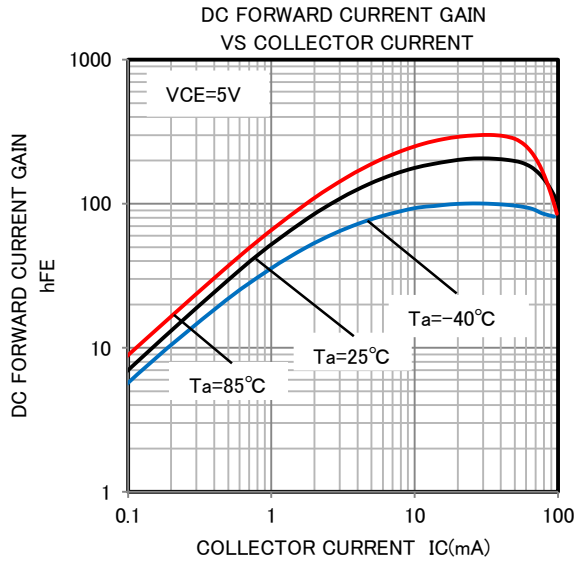
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Zener Diode

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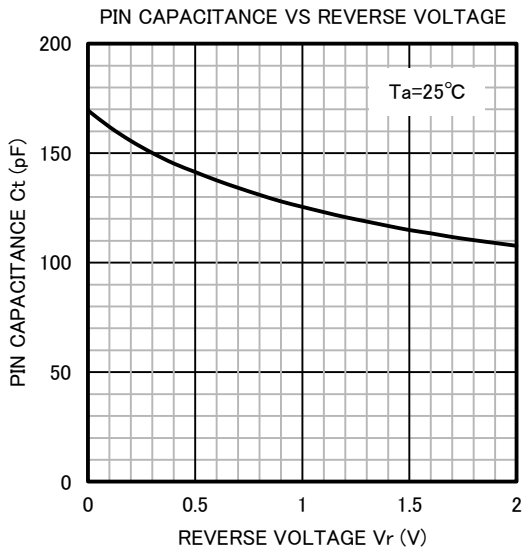
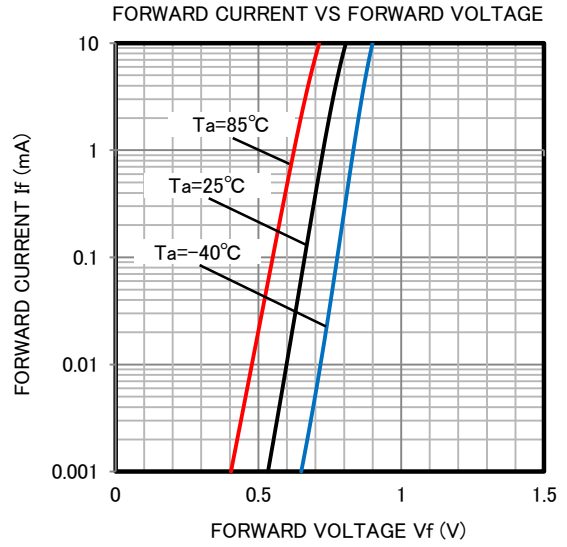
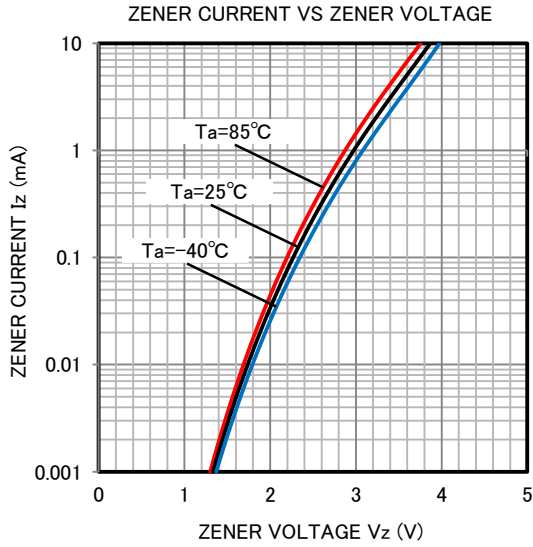
## TYPICAL CHARACTERISTICS (Tr)



# RTE05N3M-T151

Composite Transistor  
Resistive internal NPN Transistor  
Zener Diode

## TYPICAL CHARACTERISTICS (Di)



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**Keep safety first in your circuit designs!**

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